

Dual P-Channel 20 V (D-S) MOSFET

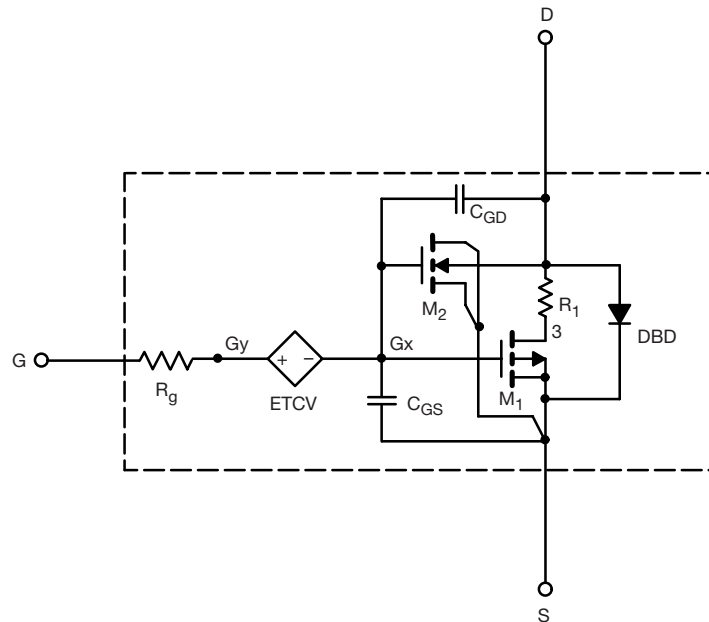
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 5 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC



Note

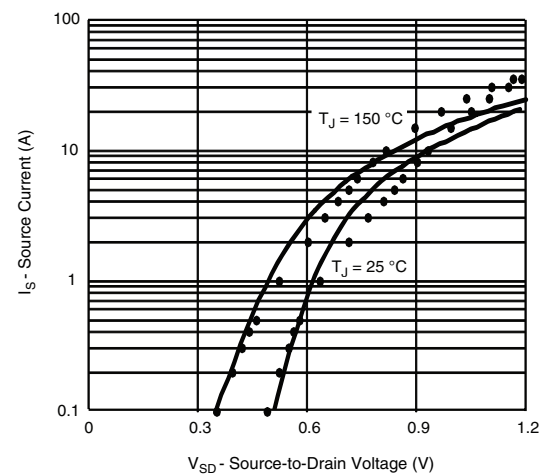
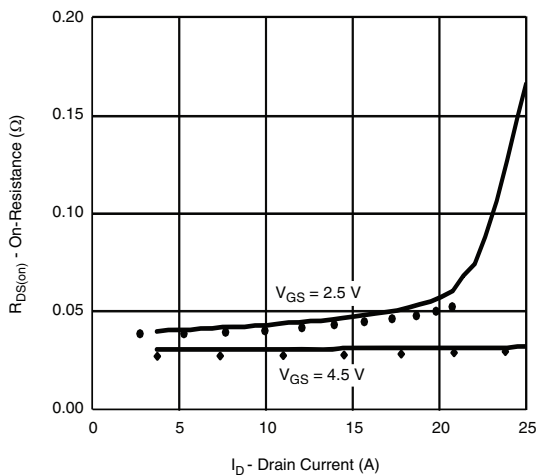
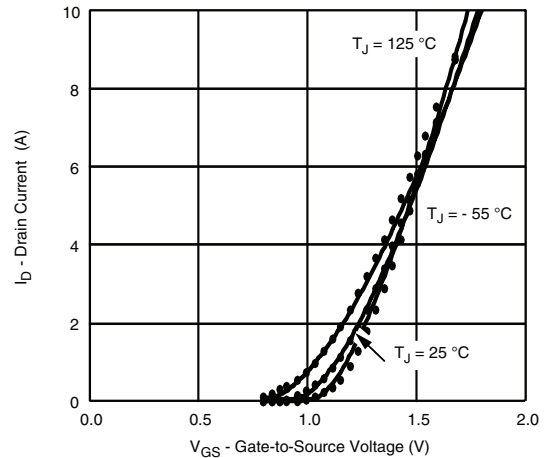
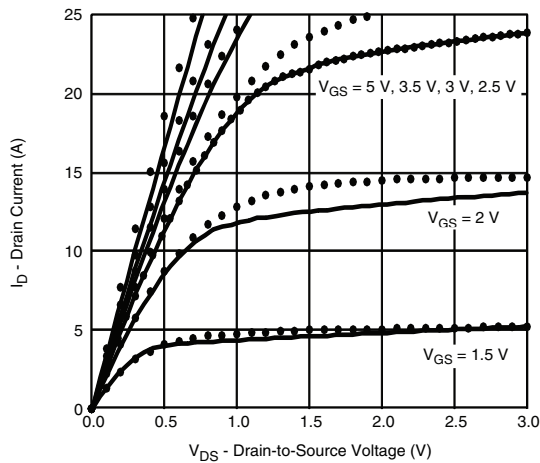
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	0.63	-	V
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\ \text{V}, I_D = -4.8\ \text{A}$	0.030	0.029	Ω
		$V_{GS} = -2.5\ \text{V}, I_D = -4\ \text{A}$	0.040	0.040	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\ \text{V}, I_D = -4.8\ \text{A}$	16	16	S
Diode Forward Voltage	V_{SD}	$I_S = -5.5\ \text{A}$	-0.80	-0.85	V

Note

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted



Note

Dots and squares represent measured data.



Disclaimer

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